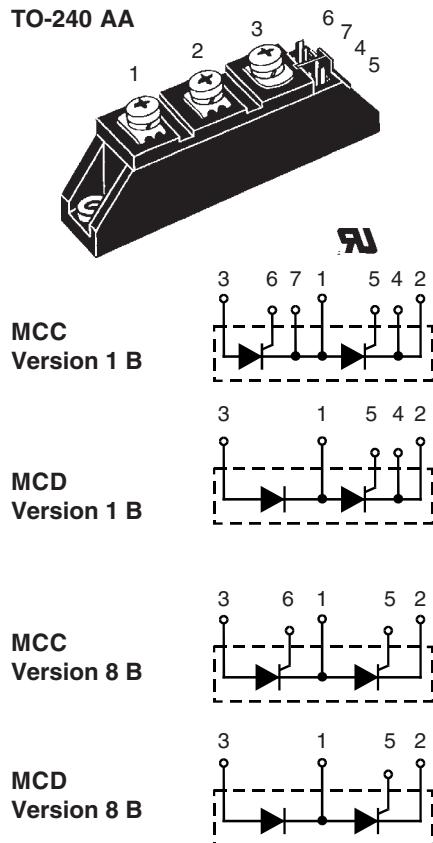


Thyristor Modules

Thyristor/Diode Modules

I_{TRMS} = 2x50 A
I_{TAVM} = 2x32 A
V_{RRM} = 800-1600 V

V _{RSM}	V _{RRM}	Type					
V _{DSM}	V _{DRM}		1 B	8 B	Version	1 B	8 B
900	800	MCC 26-08	io1 B / io8 B		MCD 26-08	io1 B / io8 B	
1300	1200	MCC 26-12	io1 B / io8 B		MCD 26-12	io1 B / io8 B	
1500	1400	MCC 26-14	io1 B / io8 B		MCD 26-14	io1 B / io8 B	
1700	1600	MCC 26-16	io1 B / io8 B		MCD 26-16	io1 B / io8 B	



Symbol	Conditions	Maximum Ratings		
I _{TRMS} , I _{FRMS}	T _{VJ} = T _{VJM}	50	A	
I _{TAVM} , I _{FAVM}	T _C = 75°C; 180° sine	32	A	
	T _C = 85°C; 180° sine	27	A	
I _{TSM} , I _{FSM}	T _{VJ} = 45°C; V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	520 560	A
	T _{VJ} = T _{VJM} V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	460 500	A
∫i ² dt	T _{VJ} = 45°C V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	1350 1300	A ² s
	T _{VJ} = T _{VJM} V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	1050 1030	A ² s
(di/dt) _{cr}	T _{VJ} = T _{VJM} f = 50 Hz, t _p = 200 µs V _D = 2/3 V _{DRM} I _G = 0.45 A di _G /dt = 0.45 A/µs	repetitive, I _T = 45 A non repetitive, I _T = I _{TAVM}	150 500	A/µs
(dv/dt) _{cr}	T _{VJ} = T _{VJM} ; R _{JK} = ∞; method 1 (linear voltage rise)	V _{DR} = 2/3 V _{DRM}	1000	V/µs
P _{GM}	T _{VJ} = T _{VJM} I _T = I _{TAVM}	t _p = 30 µs t _p = 300 µs	10 5	W
P _{GAV}			0.5	W
V _{RGM}			10	V
T _{VJ}			-40...+125	°C
T _{VJM}			125	°C
T _{stg}			-40...+125	°C
V _{ISOL}	50/60 Hz, RMS I _{ISOL} ≤ 1 mA	t = 1 min t = 1 s	3000 3600	V~
M _d	Mounting torque (M5) Terminal connection torque (M5)		2.5-4.0/22-35 Nm/lb.in 2.5-4.0/22-35 Nm/lb.in	
Weight	Typical including screws		90	g

Data according to IEC 60747 and refer to a single thyristor/diode unless otherwise stated.

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Symbol	Conditions	Characteristic Values		
I_{RRM}, I_{DRM}	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	3	mA	
V_T, V_F	$I_T, I_F = 80 \text{ A}; T_{VJ} = 25^\circ\text{C}$	1.64	V	
V_{TO}	For power-loss calculations only ($T_{VJ} = 125^\circ\text{C}$)	0.85	V	
r_T		11.0	$\text{m}\Omega$	
V_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	1.5	V	
	$T_{VJ} = -40^\circ\text{C}$	1.6	V	
I_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	100	mA	
	$T_{VJ} = -40^\circ\text{C}$	200	mA	
V_{GD}	$T_{VJ} = T_{VJM}; V_D = \frac{2}{3} V_{DRM}$	0.2	V	
I_{GD}		10	mA	
I_L	$T_{VJ} = 25^\circ\text{C}; t_p = 10 \mu\text{s}; V_D = 6 \text{ V}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$	450	mA	
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	200	mA	
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$	2	μs	
t_q	$T_{VJ} = T_{VJM}; I_T = 20 \text{ A}, t_p = 200 \mu\text{s}; -di/dt = 10 \text{ A}/\mu\text{s}$ $V_R = 100 \text{ V}; dv/dt = 20 \text{ V}/\mu\text{s}; V_D = 2/3 V_{DRM}$	typ.	150	μs
Q_s	$T_{VJ} = T_{VJM}; I_T, I_F = 25 \text{ A}, -di/dt = 0.64 \text{ A}/\mu\text{s}$	50	μC	
I_{RM}		6	A	
R_{thJC}	per thyristor/diode; DC current	0.88	K/W	
	per module	0.44	K/W	
R_{thJK}	per thyristor/diode; DC current	1.08	K/W	
	per module	0.54	K/W	
d_s	Creepage distance on surface	12.7	mm	
d_A	Strike distance through air	9.6	mm	
a	Maximum allowable acceleration	50	m/s^2	

Optional accessories for module-type MCC 26 version 1 B

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = yellow, cathode = red

Type **ZY 200L** (L = Left for pin pair 4/5) UL 758, style 1385,

Type **ZY 200R** (R = right for pin pair 6/7) CSA class 5851, guide 460-1-1

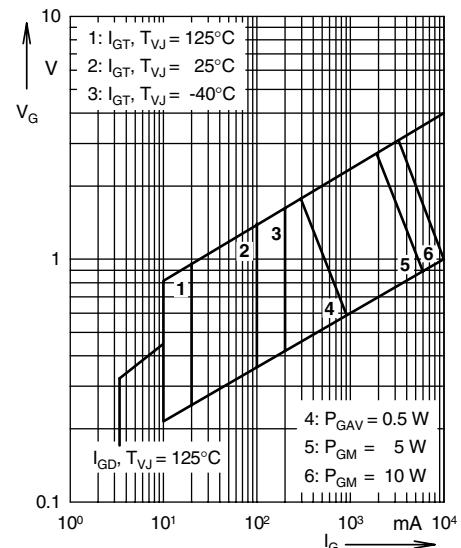


Fig. 1 Gate trigger characteristics

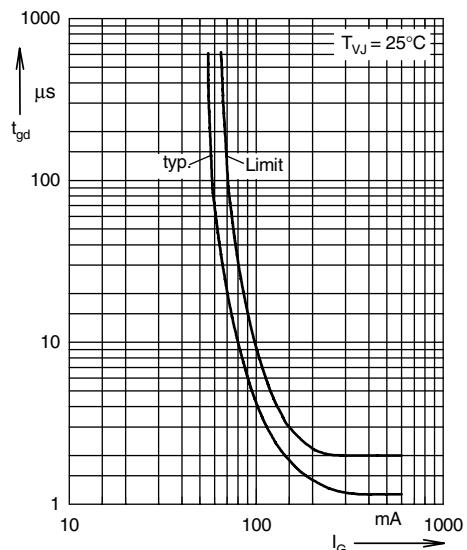
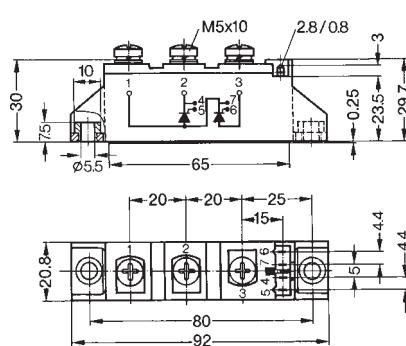


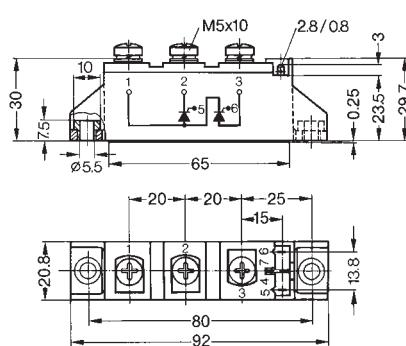
Fig. 2 Gate trigger delay time

Dimensions in mm (1 mm = 0.0394")

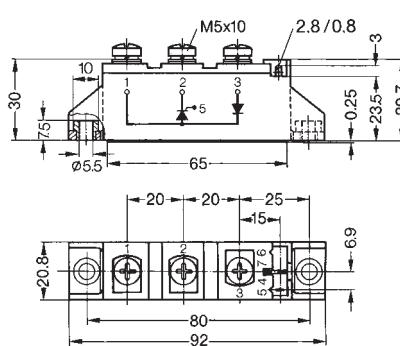
MCC Version 1 B



MCC Version 8 B



MCD Version 8 B



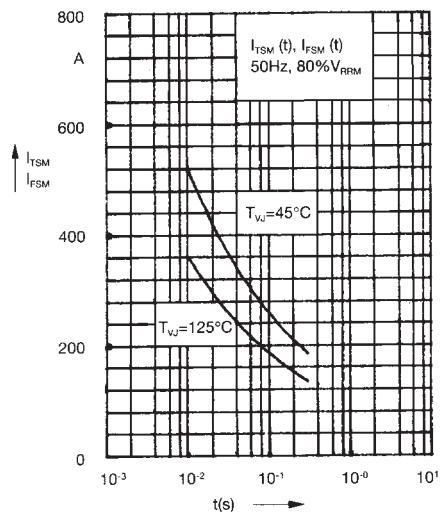


Fig. 3 Surge overload current
 I_{TSM}, I_{FSM} : Crest value, t : duration

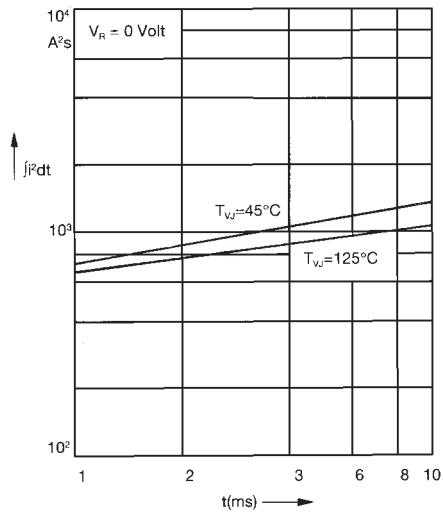


Fig. 4 $\int i^2 dt$ versus time (1-10 ms)

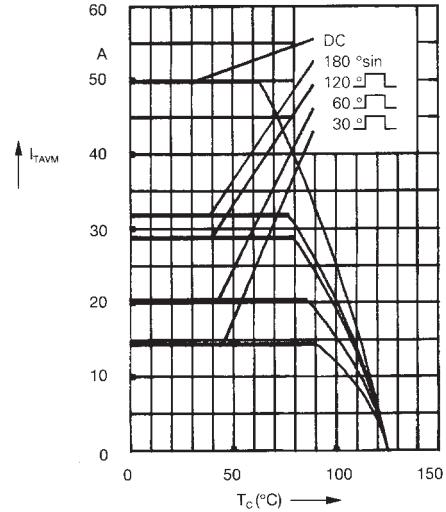


Fig. 4a Maximum forward current at case temperature

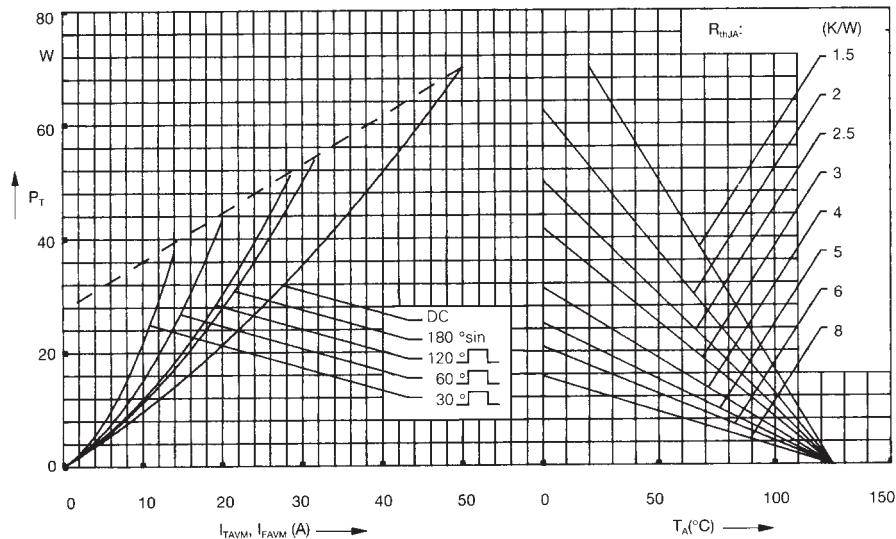


Fig. 5 Power dissipation versus on-state current and ambient temperature (per thyristor or diode)

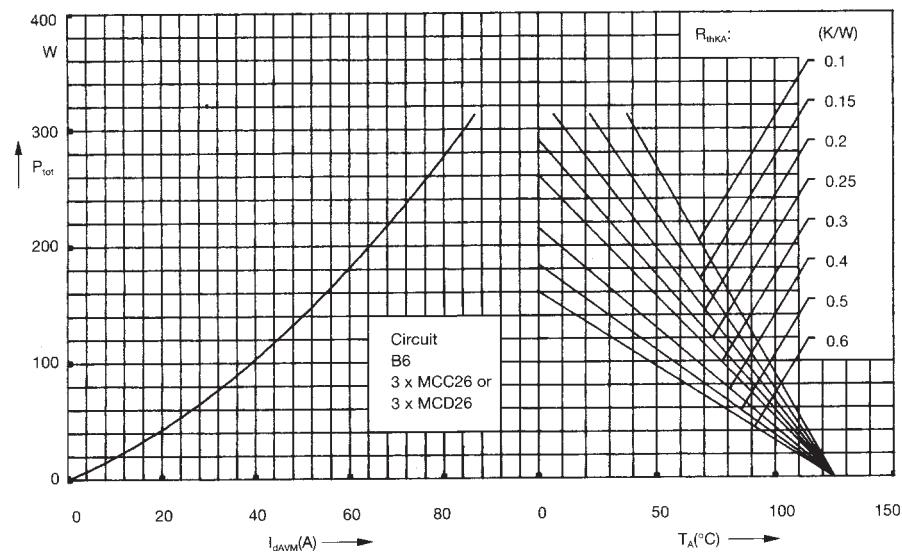
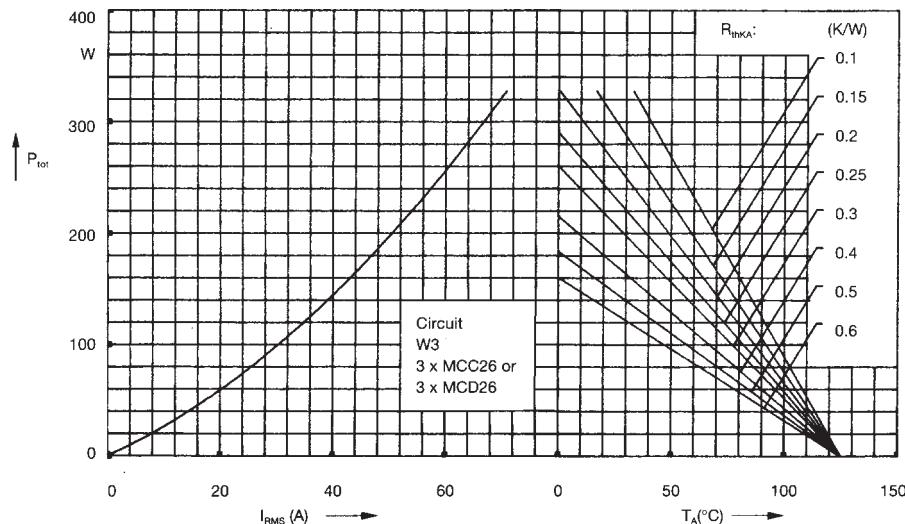


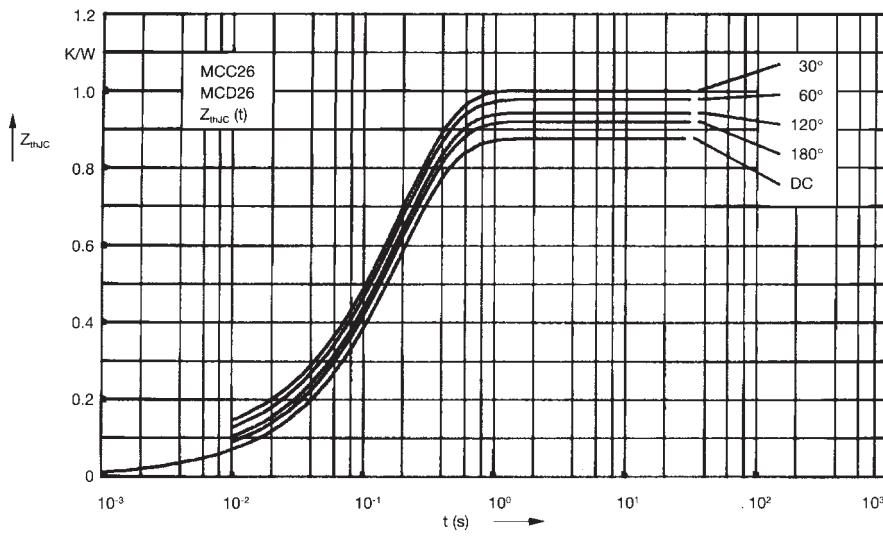
Fig. 6 Three phase rectifier bridge:
Power dissipation versus direct
output current and ambient
temperature

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**Fig. 7 Three phase AC-controller:
Power dissipation versus RMS
output current and ambient
temperature**



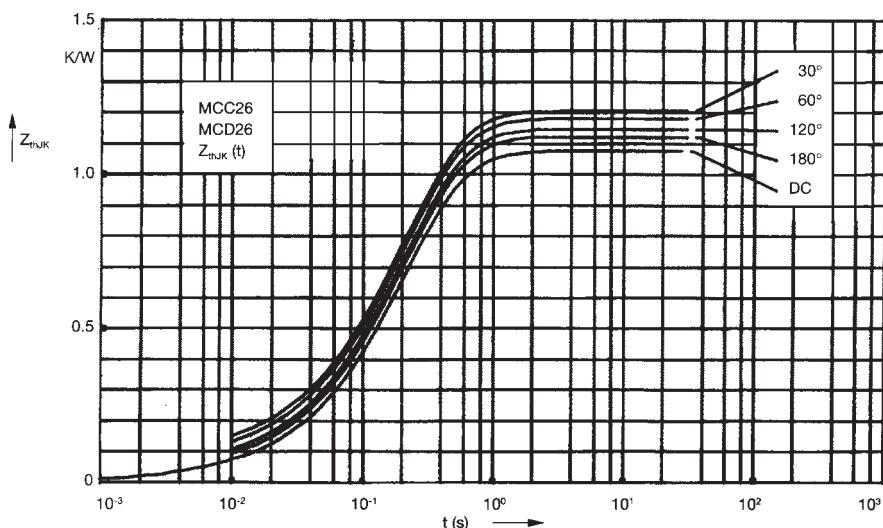
**Fig. 8 Transient thermal impedance
junction to case (per thyristor or
diode)**

R_{thJC} for various conduction angles d:

d	R_{thJC} (K/W)
DC	0.88
180°	0.92
120°	0.95
60°	0.98
30°	1.01

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.019	0.0031
2	0.029	0.0216
3	0.832	0.191



**Fig. 9 Transient thermal impedance
junction to heatsink (per thyristor or
diode)**

R_{thJK} for various conduction angles d:

d	R_{thJK} (K/W)
DC	1.08
180°	1.12
120°	1.15
60°	1.18
30°	1.21

Constants for Z_{thJK} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.019	0.0031
2	0.029	0.0216
3	0.832	0.191
4	0.2	0.45